### INTEGRATED CIRCUITS

## DATA SHEET

# **74LVT00**3.3V Quad 2-input NAND gate

Product specification

1996 Aug 15

IC24 Data Handbook





### 3.3V Quad 2-input NAND gate

**74LVT00** 

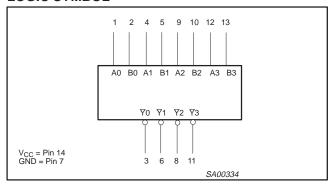
### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS T <sub>amb</sub> = 25°C; GND = 0V	TYPICAL	UNIT	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay An or Bn to Yn	C <sub>L</sub> = 50pF; V <sub>CC</sub> = 3.3V	2.7 2.7	ns	
C <sub>IN</sub>	Input capacitance	V <sub>I</sub> = 0V or 3.0V	3	pF	
I <sub>CCL</sub>	Total supply current	Outputs Low; V <sub>CC</sub> = 3.6V	1	mA	

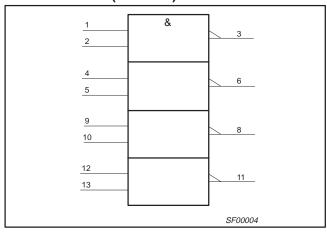
### **ORDERING INFORMATION**

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic SO	-40°C to +85°C	74LVT00 D	74LVT00 D	SOT108-1
14-Pin Plastic SSOP	-40°C to +85°C	74LVT00 DB	74LVT00 DB	SOT337-1
14-Pin Plastic TSSOP	-40°C to +85°C	74LVT00 PW	74LVT00PW DH	SOT402-1

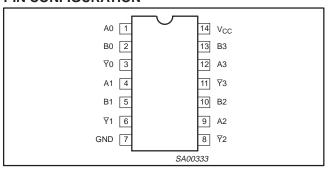
### **LOGIC SYMBOL**



### LOGIC SYMBOL (IEEE/IEC)



### **PIN CONFIGURATION**



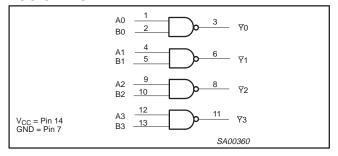
### **PIN DESCRIPTION**

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 2, 4, 5, 9, 10, 12, 13	An-Bn	Data inputs
3, 6, 8, 11	₹n	Data outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive supply voltage

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#### **LOGIC DIAGRAM**



#### **FUNCTION TABLE**

INP	JTS	OUTPUT					
Dna	Dnb	Qn					
L	L	Н					
L	Н	Н					
Н	L	Н					
Н	Н	L					

#### NOTES:

H = High voltage level L = Low voltage level

### **ABSOLUTE MAXIMUM RATINGS<sup>1, 2</sup>**

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V <sub>CC</sub>	DC supply voltage		-0.5 to +4.6	V
I <sub>IK</sub>	DC input diode current	V <sub>I</sub> < 0	-50	mA
VI	DC input voltage <sup>3</sup>		-0.5 to +7.0	V
I <sub>OK</sub>	DC output diode current	V <sub>O</sub> < 0	-50	mA
V <sub>OUT</sub>	DC output voltage <sup>3</sup>	Output in Off or High state	-0.5 to +7.0	V
	DC output ourrent	Output in High state	-32	A
IOUT	DC output current	Output in Low state	64	mA
T <sub>stg</sub>	Storage temperature range		-65 to 150	°C

#### NOTES

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the
  device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to
  absolute-maximum-rated conditions for extended periods may affect device reliability.
- The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
- 3. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

### **RECOMMENDED OPERATING CONDITIONS**

SYMBOL	PARAMETER	LIM	ITS	UNIT
STWIBOL	FARAWETER	MIN	MAX	ONIT
V <sub>CC</sub>	DC supply voltage	2.7	3.6	V
V <sub>I</sub>	Input voltage	0	5.5	V
V <sub>IH</sub>	High-level input voltage	2.0		V
V <sub>IL</sub>	Low-level Input voltage		0.8	V
Іон	High-level output current		-20	mA
I <sub>OL</sub>	Low-level output current		32	mA
Δt/Δν	Input transition rise or fall rate; Outputs enabled		10	ns/V
T <sub>amb</sub>	Operating free-air temperature range	-40	+85	°C

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#### DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions Voltages are referenced to GND (ground = 0V)

			ı			
SYMBOL	PARAMETER	TEST CONDITIONS	Temp = -	UNIT		
			MIN	TYP <sup>1</sup>	MAX	
V <sub>IK</sub>	Input clamp voltage	V <sub>CC</sub> = 2.7V; I <sub>IK</sub> = -18mA			-1.2	V
		$V_{CC} = 2.7 \text{ to } 3.6 \text{V}; I_{OH} = -100 \mu\text{A}$	V <sub>CC</sub> -0.2			
V <sub>OH</sub>	High-level output voltage	V <sub>CC</sub> = 2.7V; I <sub>OH</sub> = -6mA	2.4			V
		$V_{CC} = 3.0V; I_{OH} = -20mA$	2.0			
		V <sub>CC</sub> = 2.7V; I <sub>OL</sub> = 100μA			0.2	
$V_{OL}$	Low-level output voltage	V <sub>CC</sub> = 2.7V; I <sub>OL</sub> = 24mA			0.5	V
		V <sub>CC</sub> = 3.0V; I <sub>OL</sub> = 32mA			0.5	
,	lanut laglage ourrest	V <sub>CC</sub> = 0 or 3.6V; V <sub>I</sub> = 5.5V			10	
l <sub>l</sub>	Input leakage current	$V_{CC} = 3.6V$ ; $V_I = V_{CC}$ or GND			±1	μΑ
I <sub>OFF</sub>	Output off current	$V_{CC} = 0V$ ; $V_{I}$ or $V_{O} = 0$ to 4.5V			±100	μΑ
I <sub>CCH</sub>	Ovicement cumply ourrent	$V_{CC}$ = 3.6V; Outputs High, $V_{I}$ = GND or $V_{CC}$ , $I_{O}$ = 0			0.02	A
I <sub>CCL</sub>	Quiescent supply current	$V_{CC}$ = 3.6V; Outputs Low, $V_{I}$ = GND or $V_{CC}$ , $I_{O}$ = 0		1	2	mA
Δl <sub>CC</sub>	Additional supply current per input pin <sup>2</sup>	$V_{CC}$ = 3V to 3.6V; One input at $V_{CC}$ –0.6V, Other inputs at $V_{CC}$ or GND			0.2	μА
C <sub>I</sub>	Input capacitance	V <sub>I</sub> = 3V or 0		3		pF

- 1. All typical values are at  $V_{CC}$  = 3.3V and  $T_{amb}$  = 25°C. 2. This is the increase in supply current for each input at the specificed voltage level other than  $V_{CC}$  or GND.

### **AC CHARACTERISTICS**

GND = 0V;  $t_R$  =  $t_F$  = 2.5ns;  $C_L$  = 50pF,  $R_L$  = 500 $\Omega$ ;  $T_{amb}$  = -40°C to +85°C.

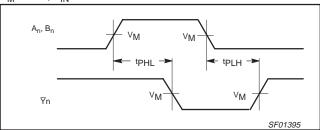
SYMBOL	PARAMETER	WAVEFORM	Vcc	$_{2}$ = 3.3V $\pm$ 0	V <sub>CC</sub> = 2.7V	UNIT	
			MIN	TYP <sup>1</sup>	MAX	MAX	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay An or Bn to Yn	1	1.0 1.0	2.7 2.7	4.1 3.9	5.0 3.8	ns

### NOTE:

1. All typical values are at  $V_{CC}$  = 3.3V and  $T_{amb}$  = 25°C.

### **AC WAVEFORMS**

 $V_{M} = 1.5V, V_{IN} = GND \text{ to } 2.7V$ 

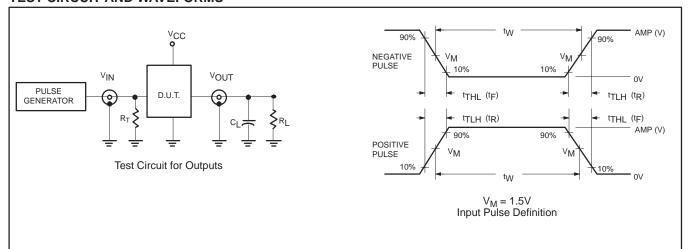


Waveform 1. Propagation delay for inverting outputs

### 3.3V Quad 2-input NAND gate

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### **TEST CIRCUIT AND WAVEFORMS**



#### **DEFINITIONS**

 $R_L$  = Load resistor; see AC CHARACTERISTICS for value.

 $C_L = Load$  capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.

FAMILY	INPUT PULSE REQUIREMENTS											
FAMILI	Amplitude	Rep. Rate	t <sub>W</sub>	t <sub>R</sub>	t <sub>F</sub>							
74LVT	2.7V	≤10MHz	500ns	≤2.5ns	≤2.5ns							

SV00022

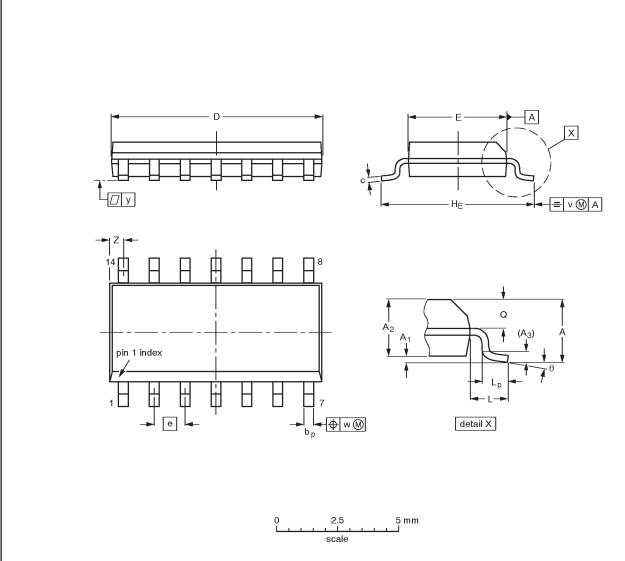
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### 3.3V Quad 2-input NAND gate

74LVT00

### SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



### DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	Α1	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	1 // //60	0.0098 0.0039		0.01		0.0098 0.0075	0.35 0.34	0.16 0.15	0.050	0.24 0.23	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT108-1	076E06\$	MS-012AB				<del>91-08-13</del> 95-01-23	

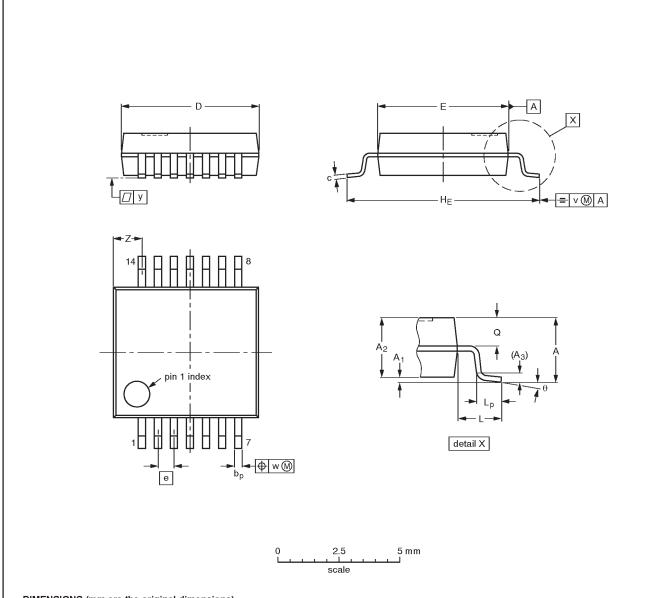
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### 3.3V Quad 2-input NAND gate

74LVT00

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



#### DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	bp	c	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

#### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE	
SOT337-1		MO-150AB				<del>95-02-04</del> 96-01-18	

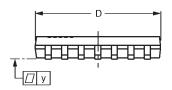
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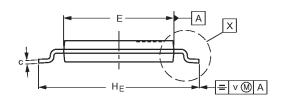
### 3.3V Quad 2-input NAND gate

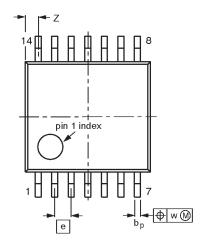
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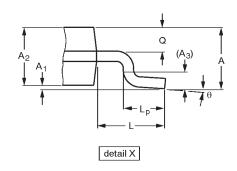
TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1











#### DIMENSIONS (mm are the original dimensions)

UNIT	A max.	Α1	A <sub>2</sub>	A <sub>3</sub>	bр	c	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				<del>94-07-12</del> 95-04-04	

### 3.3V Quad 2-input NAND gate

74LVT00

**NOTES** 

### 3.3V Quad 2-input NAND gate

74LVT00

DEFINITIONS							
Data Sheet Identification	Product Status	Definition					
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.					
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(print code) Date of release: July 1994

Document order number: 9397-750-04847

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